

Guangdong Yuejing High Technology CO.,LTD.

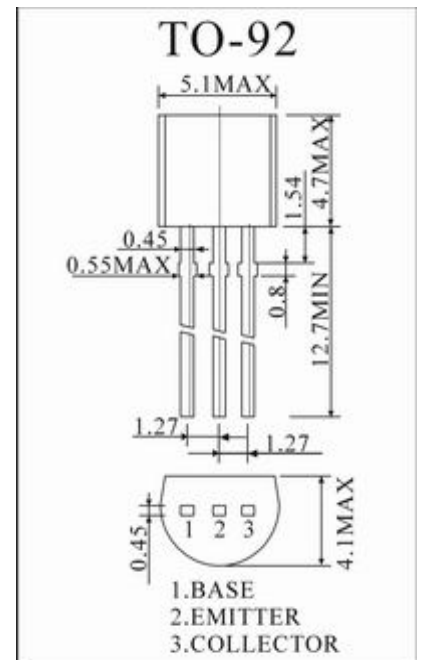
MPSH10

—NPN silicon—

■ ■ APPLICATION: Low noise UHF/VHF amplifiers Applications.

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	3	V
Collector current	I _c	50	mA
Collector Power Dissipation	P _c	350	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	60				V _{CE} = 10V, I _c = 4mA
Collector Cut-off Current	I _{CBO}			0.1	μA	V _{CB} = 25V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 2V, I _c =0
Collector-Base Breakdown Voltage	BV _{CBO}	30			V	I _c = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	25			V	I _c = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	3			V	I _E = 0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.2	0.5	V	I _c = 4mA, I _B = 0.4mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			1	V	I _c = 4mA, I _B = 0.4mA
Gain bandwidth product	f _T	650			MHz	I _c = 4mA, V _{CE} = 10V
Common Base Output Capacitance	C _{ob}			2	PF	V _{CB} = 10V, I _E =0, f=1MHz

■ ■ h_{FE} Classification And Marking

Classification

h_{FE} >60